

isc Silicon NPN Power Transistors

2SD426

DESCRIPTION

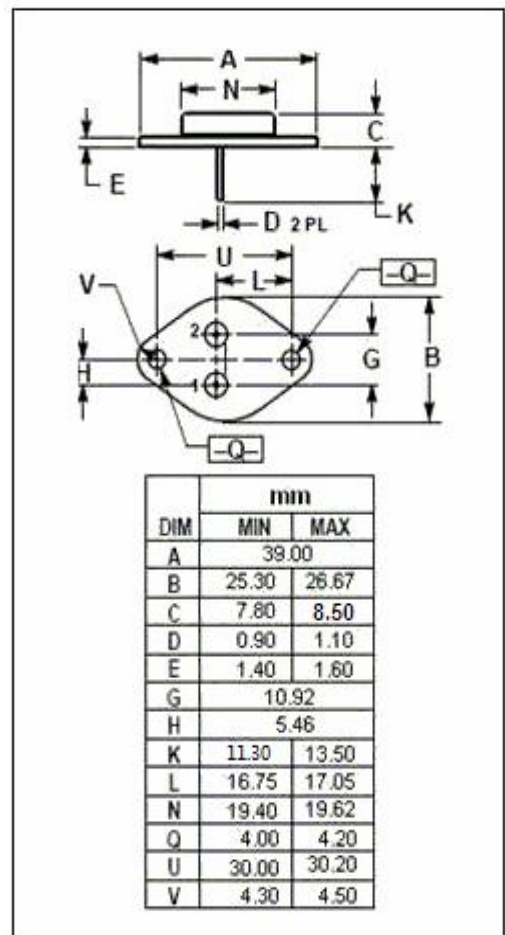
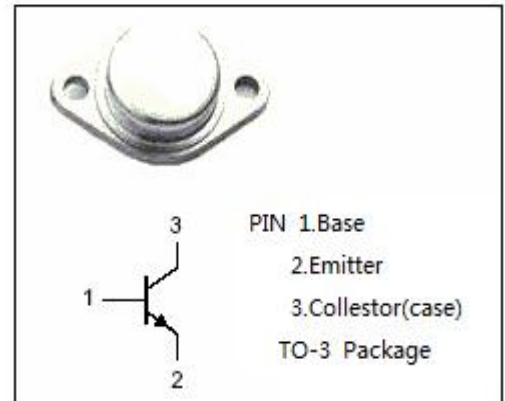
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 120V(\text{Min})$
- High Power Dissipation-
: $P_C = 100W(\text{Max})@T_C=25^\circ\text{C}$
- Complement to Type 2SB556
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for power amplifier applications.
- Recommended for high-fidelity audio frequency amplifier output stage.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | 120 | V |
| V_{CEO} | Collector-Emitter Voltage | 120 | V |
| V_{EBO} | Emitter-Base Voltage | 5 | V |
| I_C | Collector Current-Continuous | 12 | A |
| I_E | Emitter Current-Continuous | 12 | A |
| P_C | Collector Power Dissipation @ $T_C=25^\circ\text{C}$ | 100 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | -65~150 | $^\circ\text{C}$ |



isc Silicon NPN Power Transistors**2SD426****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 10mA; I _B = 0 | 120 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 1mA; I _C = 0 | 5 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 6A; I _B = 0.6A | | | 3.0 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = 7A; V _{CE} = 5V | | | 2.5 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 60V; I _E = 0 | | | 0.1 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 0.1 | mA |
| h _{FE} | DC Current Gain | I _C = 2A; V _{CE} = 5V | 40 | | 140 | |
| C _{OB} | Output Capacitance | I _E = 0; V _{CB} = 10V; f= 1MHz | | 330 | | pF |
| f _T | Current-Gain—Bandwidth Product | I _E = -2A; V _{CE} = 5V | | 6 | | MHz |

◆ **h_{FE} Classifications**

| R | O |
|-------|--------|
| 40-80 | 70-140 |

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.